

isc Silicon PNP Darlington Power Transistor

2SB1567

DESCRIPTION

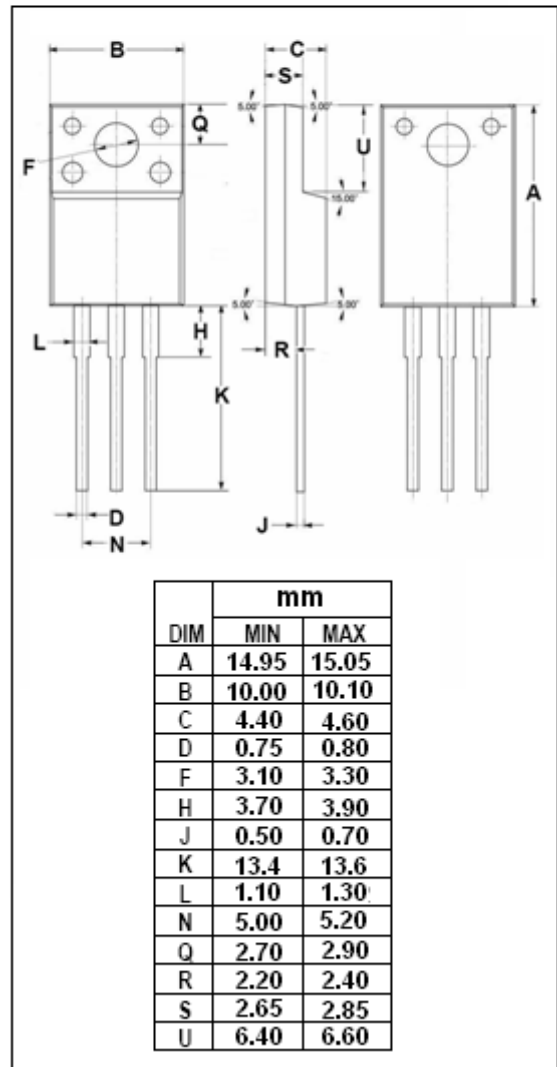
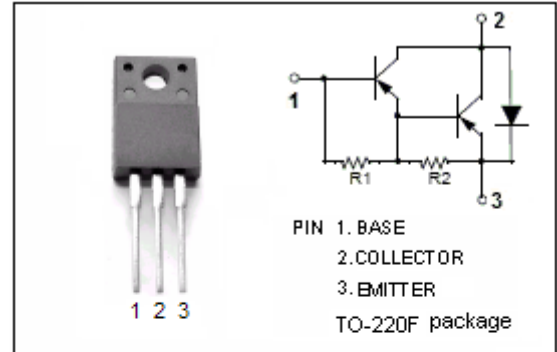
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min})@ (V_{CE} = -2V, I_C = -1A)$
- Complement to Type 2SD2398

APPLICATIONS

- Designed for high power switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Darlington Power Transistor**2SB1567****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -5mA; I _B = 0	-100			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -50 μ A; I _E = 0	-100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1A; I _B = -1mA			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7V; I _C = 0			-3.0	mA
h _{FE}	DC Current Gain	I _C = -1A; V _{CE} = -2V	1000		10000	
C _{OB}	Collector Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		35		pF